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Data Sheet

LED Chip blue-green

EOLC-505-34

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Radiation	Type	Electrodes
blue-green	GaN / sapphire	P + N up

Diagram	Description
	<p>Description</p> <ul style="list-style-type: none"> - Substrate: sapphire, epitaxial layer: GaN based material - N bonding pad electrode: Au alloy - P bonding pad electrode: Au alloy <p>Above drawing is not on real scale</p>

Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$, $t_p/T = 1/2$	I_{FM}			100	mA

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		3.3	3.5	V
Reverse current	$V_R = 5 \text{ V}$	I_R			1	μA
Luminous intensity*	$I_F = 20 \text{ mA}$	I_v	300	400	500	mcd
Luminous flux*	$I_F = 20 \text{ mA}$	Φ_v		1700		mlm
Radiant intensity*	$I_F = 20 \text{ mA}$	I_e		1.1		mW/sr
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e		7.4		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p		502		nm
Dominant wavelength	$I_F = 20 \text{ mA}$	λ_D	502	505	508	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		30		nm

*Measured on bare chip on TO-18 header

Packing: Chips on adhesive film with wire-bond side top

Art. No. 112 030



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.